

What is claimed is:

1. A [crystal] quartz thin film made by depositing at least one silicon alkoxide selected from the group consisting of tetramethoxysilane, tetraethoxysilane, tetrapropoxysilane and tetrabutoxysilane on a substrate under atmospheric pressure.

2. A [crystal] quartz thin film as claimed in claim 1, which is a [crystal] quartz epitaxial thin film.